

Specifications

■ INFRARED EMITTING DIODES

MODEL: SIR204/SIR333

■ GENERAL DESCRIPTION

The SIR204 and SIR333 are super-high-efficiency Gallium Aluminum Arsenide (GaAlAs) Infrared Emitting Diodes encapsulated in blue transparent plastic T-1 or T-1½ package

■ ELECTRICAL AND RADIANT CHARACTERISTICS (T=25°C)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNIT	TEST CONDITION
V_F	Forward Voltage		1.3	1.7	V	$I_F = 100mA$
I_R	Reverse Leakage Current			10	μA	$V_A = 5.0V$
P_D	Radiant Power	21	35		mW	$I_F = 100mA$
λ_p	Peak Spectral Wavelength		880		nm	$I_F = 100mA$

MODEL: IR204/IR333

■ GENERAL DESCRIPTION

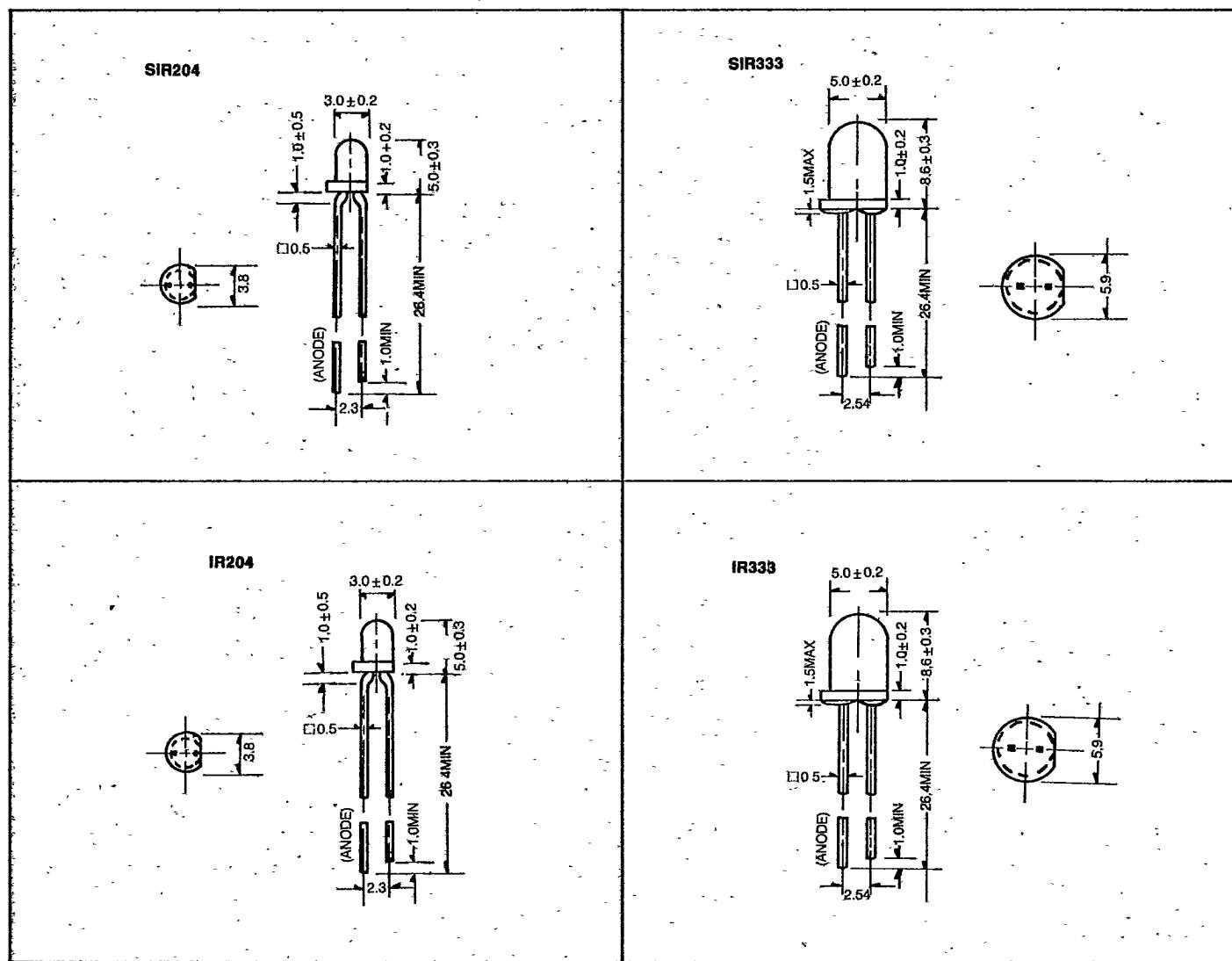
The IR204 and IR333 are high power solution grown Epitaxial Gallium Arsenide Infrared Emitting Diodes encapsulated in blue transparent plastic T-1 or T-1½ package

■ ELECTRICAL AND RADIANT CHARACTERISTICS (T=25°C)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNIT	TEST CONDITION
V_F	Forward Voltage		1.3	1.7	V	$I_F = 100mA$
I_R	Reverse Leakage Current			10	μA	$V_A = 5.0V$
P_D	Radiant Power	6	10		mW	$I_F = 100mA$
λ_p	Peak Spectral Wavelength		940		nm	$I_F = 100mA$
$\Delta\lambda_p$	Spectral Bandwidth Between Half-Power		40		nm	$I_F = 100mA$

■ PACKAGE DIMENSIONS: INFRARED EMITTING DIODES

NOTE: 1. All dimensions are in millimeters. 2. Lead spacing is measured where the leads emerge from the package. 3. Protruded resin under flange 1.5 mm (0.059") Max.



■ ABSOLUTE MAXIMUM RATINGS (25°C unless otherwise noted)

● Continuous Forward Current	100mA
● Peak Forward Current (Pulse Width = 10µs, 1% duty cycle)	1.2A
● Reverse Voltage	5V
● Operating Temperature Range	-40°C to +85°C
● Storage Temperature Range	-40°C to +85°C
● Lead Soldering Temperature (1/16 inch from body for 5 sec)	240°C
● Relative Humidity at 85°C	85%
● Power Dissipation at (or below) 25°C Free Air Temperature	150mW